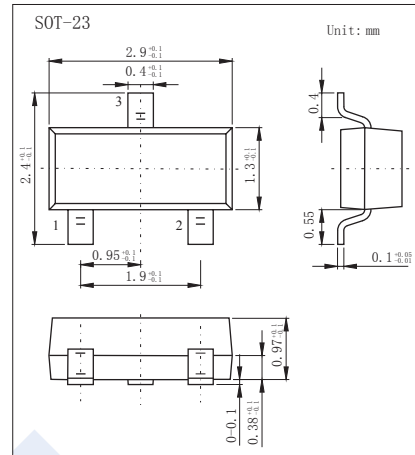
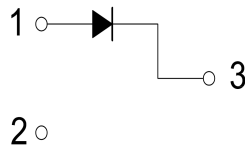


Schottky Diodes

RB421D (KB421D)

■ Features

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	V_{RM}	40	V
DC Blocking Voltage	V_R	40	
Average Rectified Output Current	I_o	0.1	A
Peak Forward Surge Current	I_{FM}	1	
Power Dissipation	P_D	250	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	400	$^\circ\text{C/W}$
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100 \mu\text{A}$	40			V
Forward voltage	V_F	$I_F = 10\text{mA}$			0.34	
		$I_F = 100\text{mA}$			0.55	
Reverse voltage leakage current	I_R	$V_R = 10 \text{ V}$			30	μA
Capacitance between terminals	C_T	$V_R = 10 \text{ V}, f = 1 \text{ MHz}$		6		pF

■ Marking

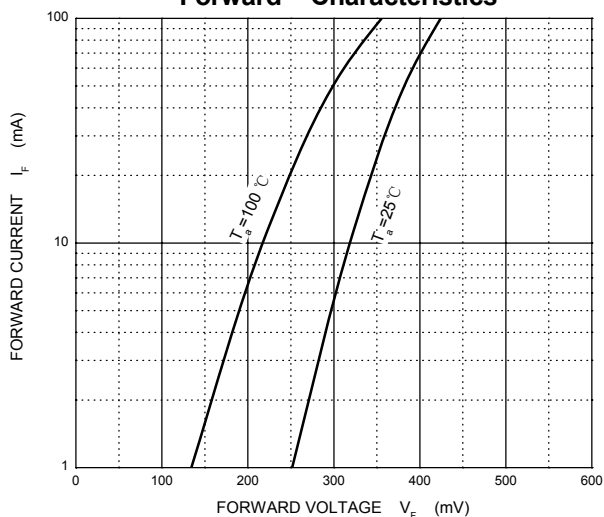
Marking	D3C
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Schottky Diodes

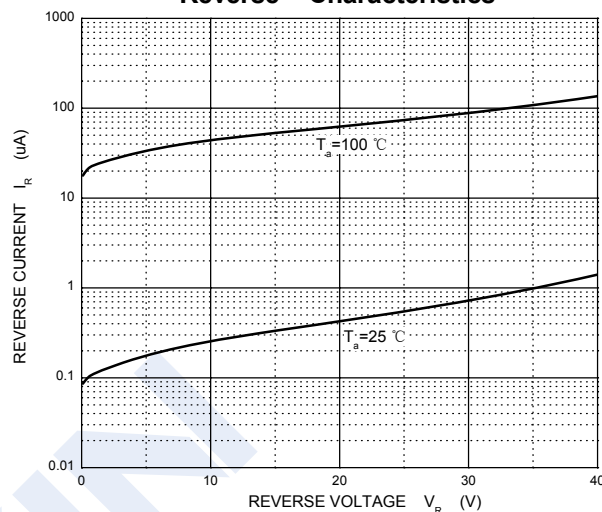
RB421D (KB421D)

■ Typical Characteristics

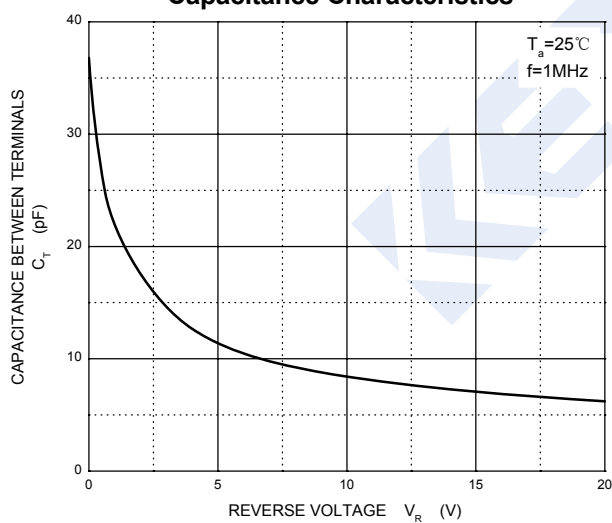
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

